

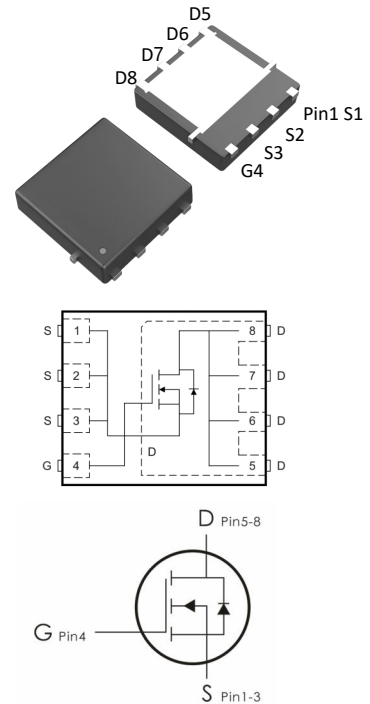
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=12V, I_D=90A, R_{DS(ON)} < 2.3m\Omega @ V_{GS}=4.5V$ (Typ: $2.1m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
ZA2R3NAG	A2R3NA	DFN3*3-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	12	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current ¹	90	A
	Continuous Drain Current- $T_c=100^\circ C$ ¹	63	
I_{DM}	Pulsed Drain Current ²	360	
P_D	Power Dissipation	42	W
E_{AS}	Single pulse avalanche energy ³	110	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55--+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	$^\circ C/W$

Electrical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	12	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =12V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 12V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	0.4	0.7	1	V
R _{DS(ON)}	Drain-Source On Resistance ⁴	V _{GS} =4.5V, I _D =10A	---	2.1	2.3	m Ω
		V _{GS} =2.5V, I _D =5A	---	2.8	3.5	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	4000	---	pF
C _{oss}	Output Capacitance		---	459	--	
C _{rss}	Reverse Transfer Capacitance		---	445	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =10V, I _D =30A, R _G =1.8 Ω ,V _{GS} =10V	---	9.7	---	ns
t _r	Rise Time		---	36	---	ns
t _{d(off)}	Turn-Off Delay Time		---	62	---	ns
t _f	Fall Time		---	52	---	ns
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =30A	---	50	---	nC
Q _{gs}	Gate-Source Charge		---	3.5	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	18	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =30A	---	---	1.2	V
I _S	Continuous Drain Current	V _D =V _G =0V	---	---	75	A
I _{SM}	Pulsed Drain Current		---	---	300	A
T _{rr}	Reverse Recovery Time	I _F =30A, T _J =25 °C	---	23	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/us	---	109	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C, V_{DD}=6V, V_G=10V, L=0.5mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Test Circuit

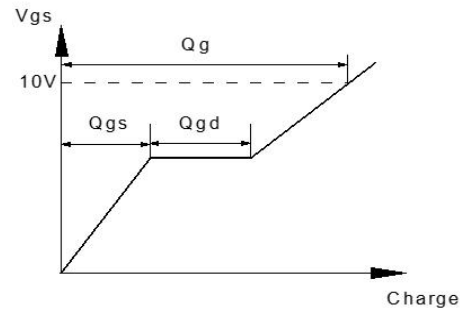
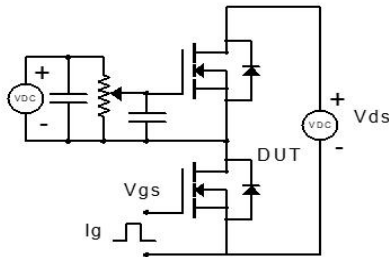


Figure 1: Gate Charge Test Circuit & Waveform

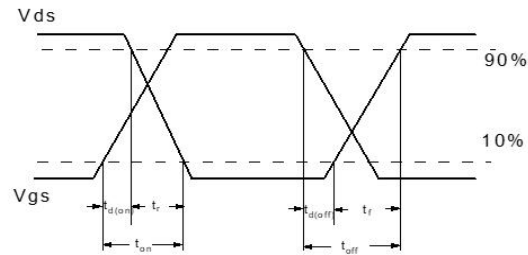
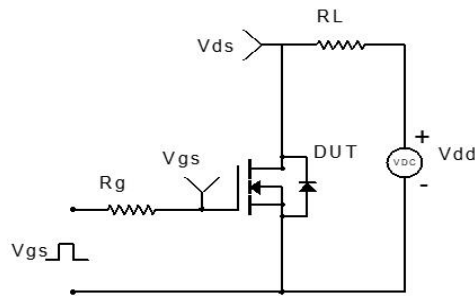


Figure 2: Resistive Switching Test Circuit & Waveform

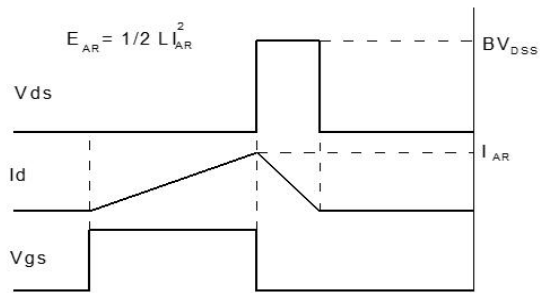
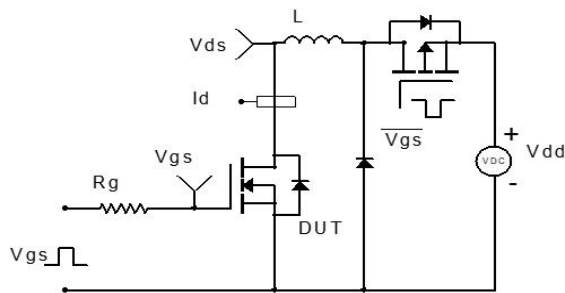


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

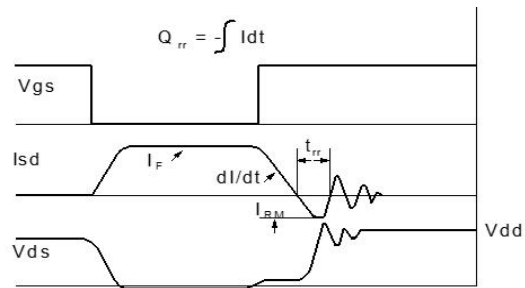
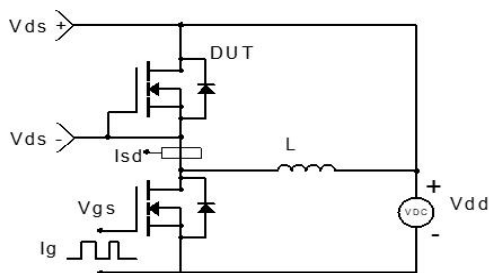
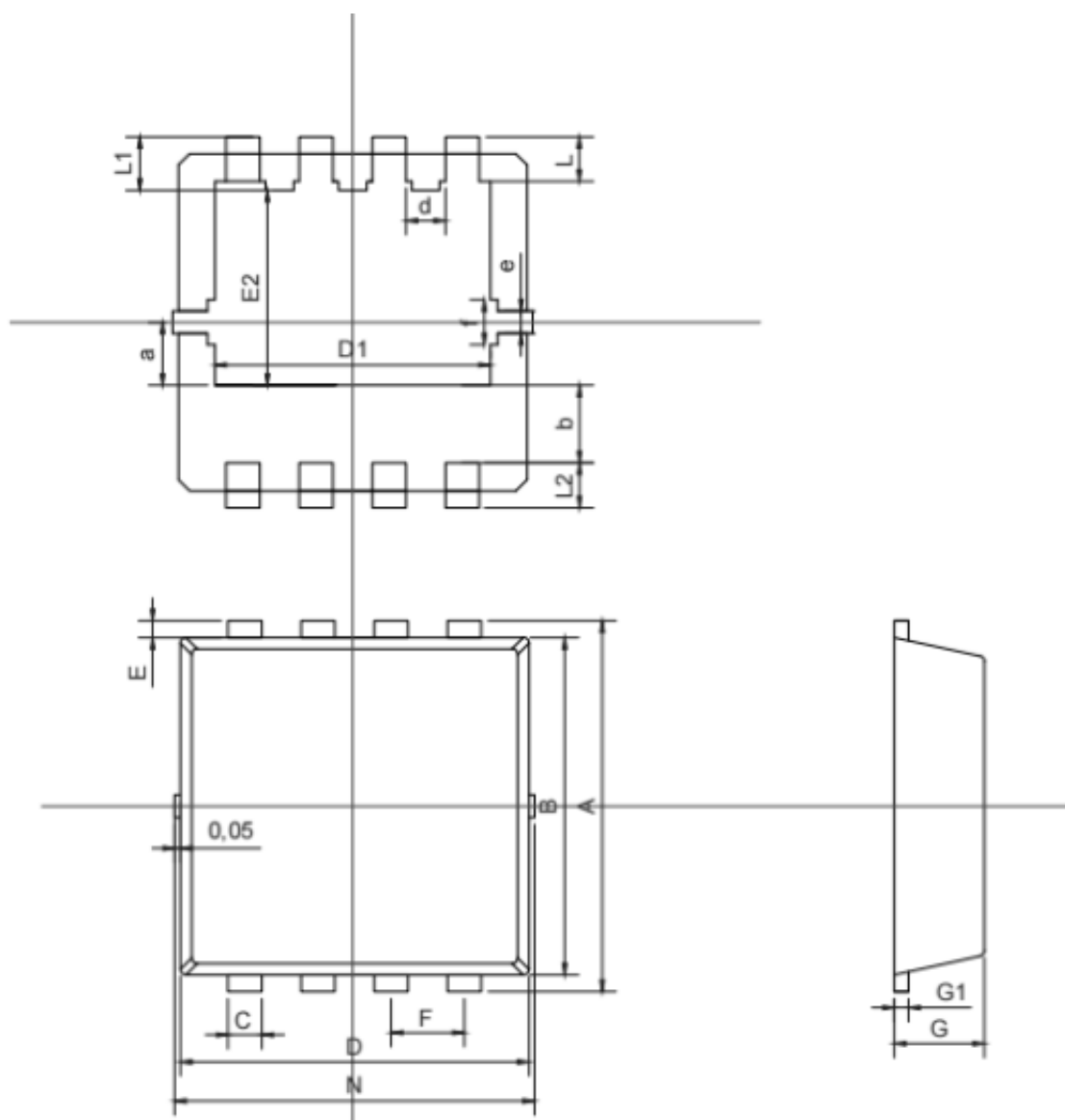


Figure 4: Diode Recovery Test Circuit & Waveform

DFN3X3-8 Package Information:

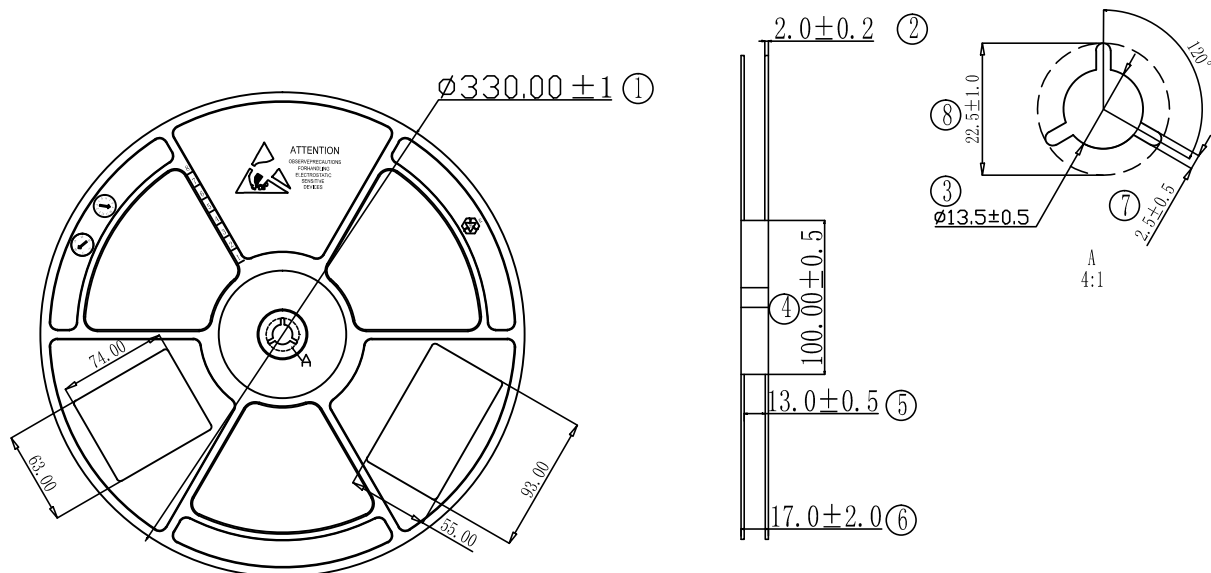


Dimensions

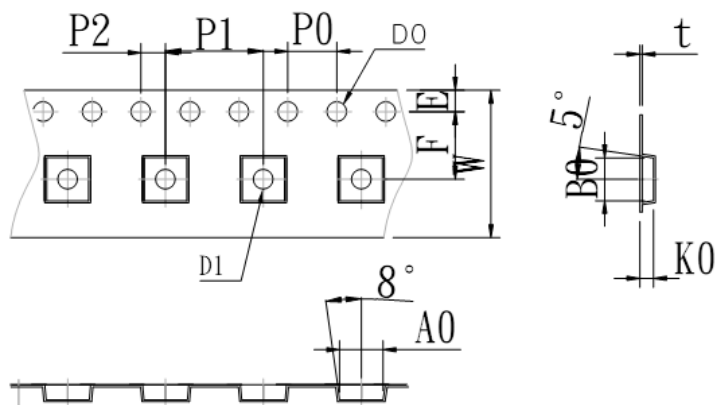
Unit	A	B	C	D	E	F	G	G1	D1	L	N	E2	L1	L2	a	b	d	e	f	n
mm	3.25 (3.35) 3.45	2.95 (3.05) 3.15	0.25 (0.30) 0.35	3.05 (3.10) 3.15	0.12 (0.15) 0.20	— (0.65) —	0.75 (0.80) 0.85	0.135 (0.15) 0.17	2.40 (2.45) 2.50	0.365 (0.41) 0.565	3.15 (3.20) 3.25	1.685 (1.73) 1.785	0.43 (0.48) 0.53	0.35 (0.40) 0.45	0.515 (0.56) 0.615	0.635 (0.68) 0.735	0.35 (0.40) 0.45	0.17 (0.20) 0.25	0.37 (0.40) 0.45	2.08 (2.58) 3.08

Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	3.55 $\pm$ 0.10	3.45 $\pm$ 0.10	1.13 $\pm$ 0.10	1.55 $\pm$ 0.10	1.55 $\pm$ 0.10	4.00 $\pm$ 0.10	8.00 $\pm$ 0.10	40.0 $\pm$ 0.10
Symbol	W	E	F	P2	t			
Spec	12.00 $\pm$ 0.10	1.75 $\pm$ 0.10	5.50 $\pm$ 0.10	2.00 $\pm$ 0.10	0.20 $\pm$ 0.05			



Pulling direction →

Marking Information:

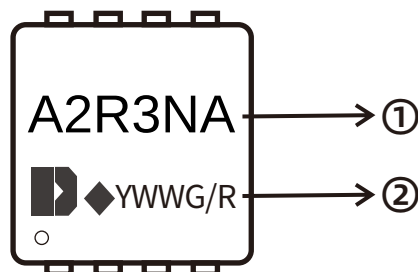
①. Part NO.

②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2026-04-10	Release of final version

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